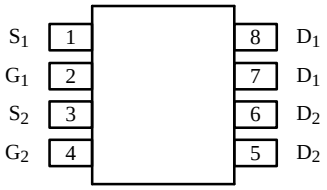
Dual N-Channel Enhancement-Mode MOSFET

Product Summary

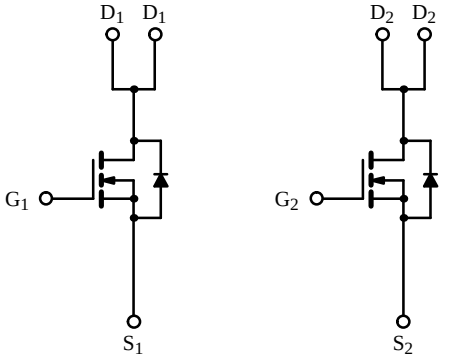
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.30 @ V_{GS} = 10 V	± 2.0
	0.50 @ V_{GS} = 5 V	± 0.6

For higher performance see Si9945DY

SO-8



Top View



N-Channel MOSFET N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	± 2.0	A
	T_A = 70°C		± 1.6	
Pulsed Drain Current		I_{DM}	± 8	
Continuous Source Current (Diode Conduction)[a]		I_S	1.8	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2	W
	T_A = 70°C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient[a]	R_{thJA}	62.5	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

Subsequent updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #1224. A SPICE Model data sheet is available for this product (FaxBack document #5116).

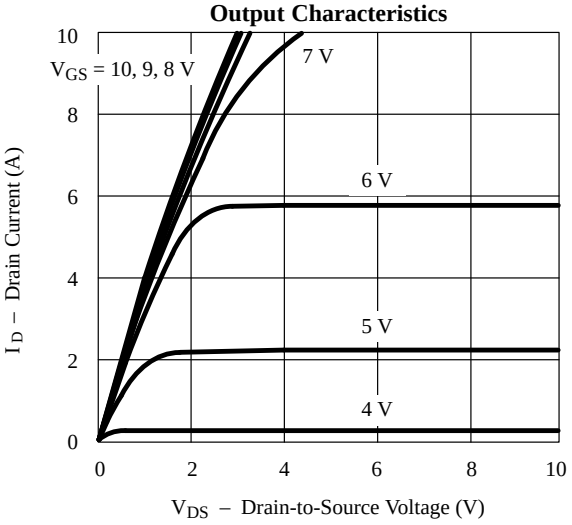
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48 V, V_{GS} = 0 V			2	µA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	8			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 1.5 A		0.23	0.30	Ω
		V_{GS} = 5 V, I_D = 0.6 A		0.32	0.50	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 2.0 A		2.5		S
Diode Forward Voltage[b]	V_{SD}	I_S = 1.25 A, V_{GS} = 0 V		0.85	1.2	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = 25 V, V_{GS} = 10 V, I_D = 1.3 A		5	15	nC
Gate-Source Charge	Q_{gs}			1		
Gate-Drain Charge	Q_{gd}			2		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 50 Ω I_D ≅ 0.6 A, V_{GEN} = 10 V, R_G = 6 Ω		7	40	ns
Rise Time	t_r			18	70	
Turn-Off Delay Time	$t_{d(off)}$			40	100	
Fall Time	t_f			23	70	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.25 A, di/dt = 100 A/µs		70	100	

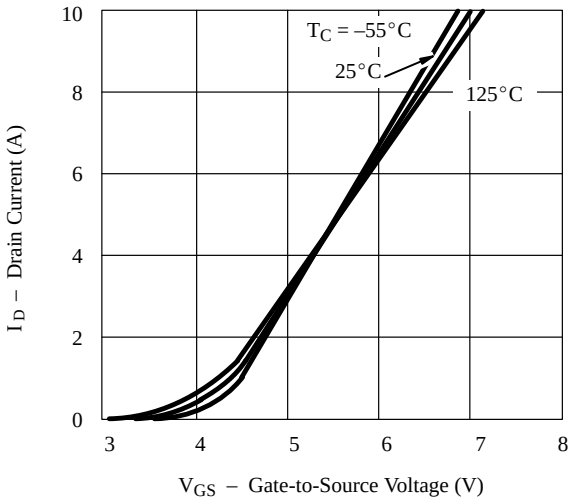
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.

Typical Characteristics (25°C Unless Otherwise Noted)

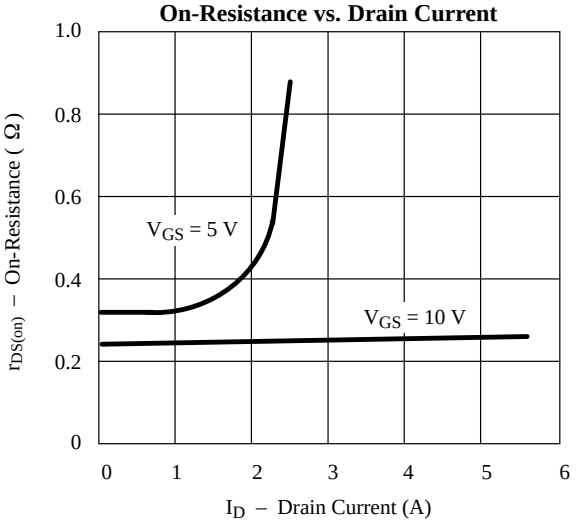
Output Characteristics



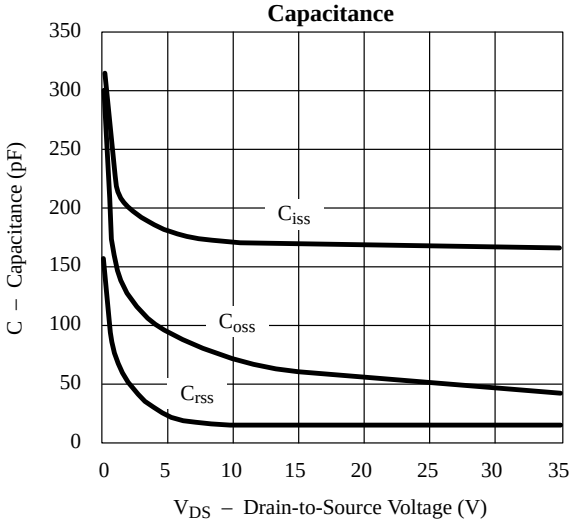
Transfer Characteristics



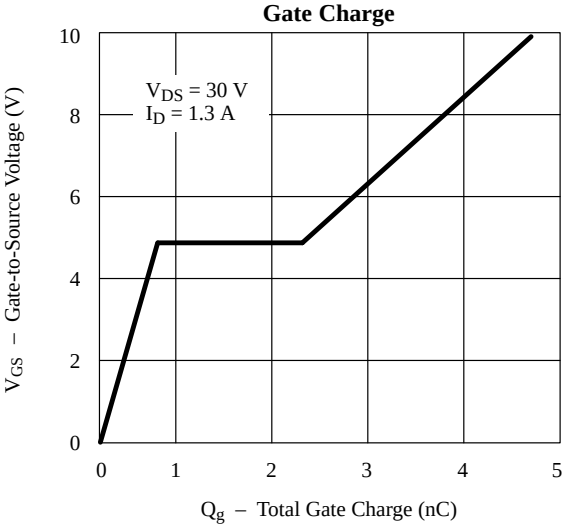
On-Resistance vs. Drain Current



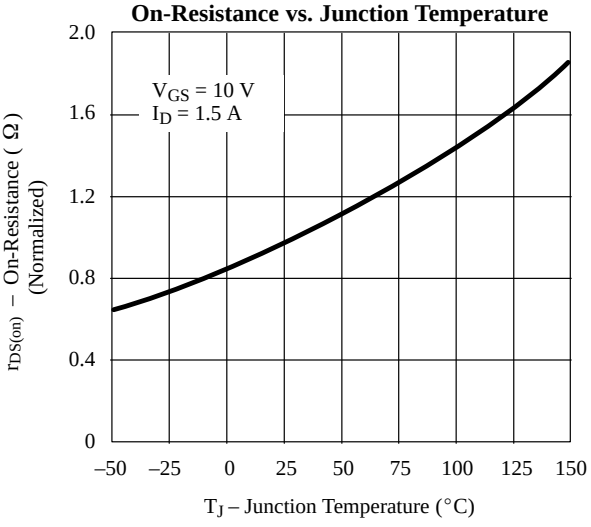
Capacitance



Gate Charge

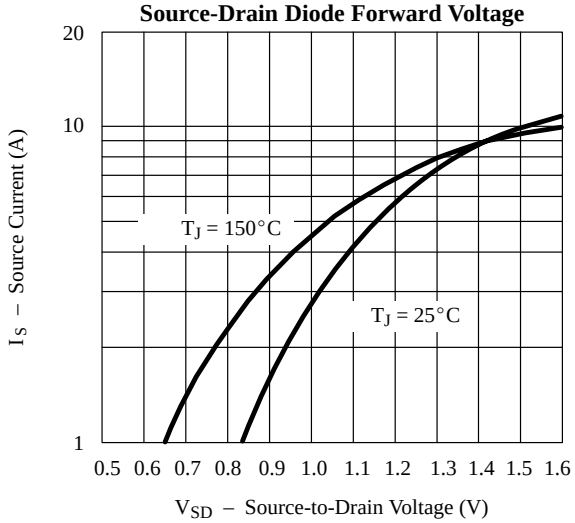


On-Resistance vs. Junction Temperature

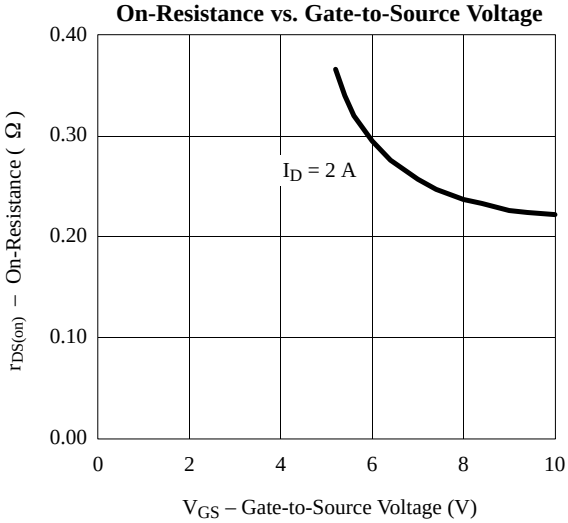


Typical Characteristics (25°C Unless Otherwise Noted)

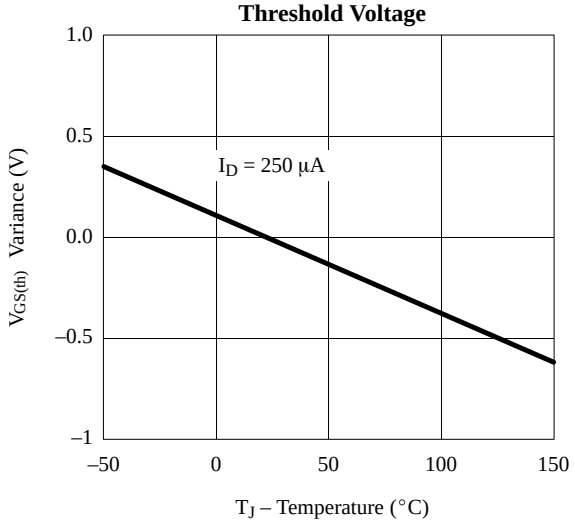
Source-Drain Diode Forward Voltage



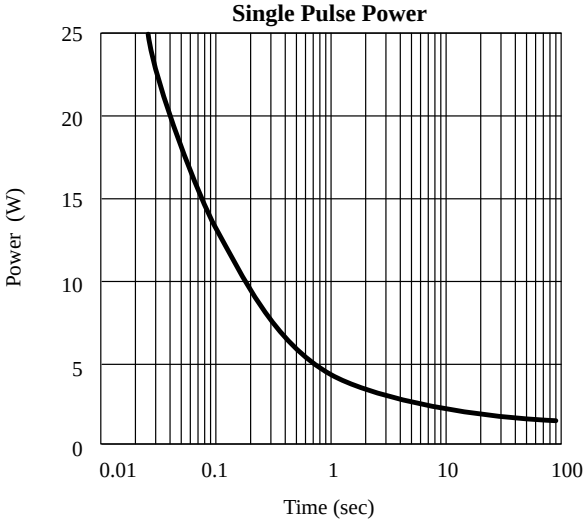
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient